1. Scope :

This specification applies to PIN silscon photodiode chips,
Device No. PD-0043

2. Structure :

2-1. Planar type : PIN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy .

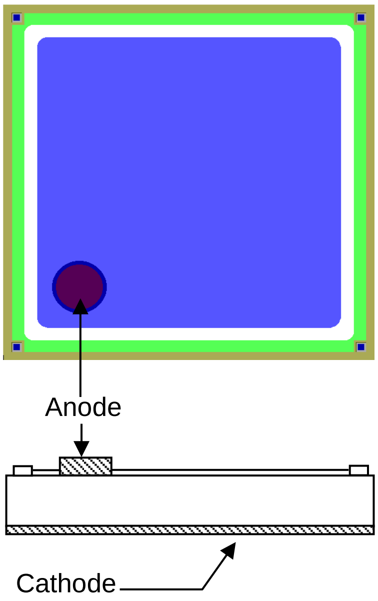
3. Size :

3-1. Chip size : 43 mils × 43 mils (1.095 mm × 1.095 mm).
3-2. Chip thickness : 12 ± 1.5mils (0.305 ± 0.038mm).
3-3. Active area : 35.24 mils × 35.24 mils (0.895 mm × 0.895 mm).
3-4. Bonding pad (Anode) : 6.30 mils (0.160 mm)diameter.
3-5. Pattern drawing : Refer to the attached drawing.

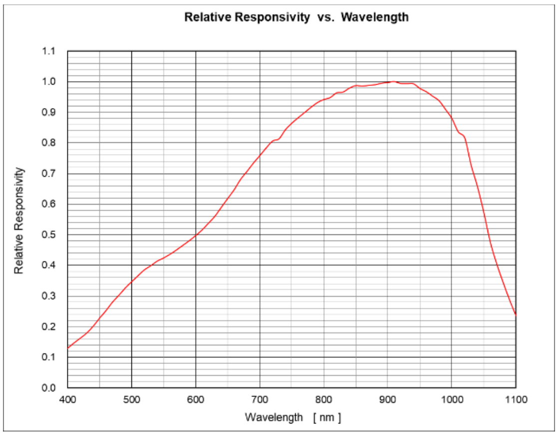
4. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark current	I_D	V_R=10V Ee=0mW/cm^2			10	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100uA Ee =0mW/cm^2	60			V
Open circuit voltage	Voc	T=2856K Ee =5mW/cm^2		350		mV
Short circuit Current	Isc	T=2856K Ee=5mW/cm^2		8		μA
Reverse light current	I_L	V_R =5V T=2856K Ee=5mW/cm^2		8		μA
Total Capacitance	C_t	V_R =5V Ee=0mW/cm^2 f=1MHz		2.5		pF

※Based on 100% probing



5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.